

The background of the cover is a detailed, colorful micrograph of a microelectronic circuit. It shows a complex network of thin, metallic lines (interconnects) and various components like transistors and capacitors, all arranged in a precise, grid-like pattern. The colors range from bright yellow and orange to deep blue and purple, highlighting the intricate details of the chip's surface.

SECOND EDITION

MICROELECTRONIC CIRCUIT DESIGN

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SOLID STATE ELECTRONIC AND DEVICES

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